Special Issue

RRAM Devices: Materials, Designs, and Properties

Message from the Guest Editor

The incremental advancement of complementary metal-oxide-semiconductor (CMOS) technologies is quickly approaching its physical and economical limitations. As such, many researchers have been looking for alternative ways of addressing the problems in develop future generation memory devices that offer higher integration density and lower power consumption than the commercialized memory based on the current technologies. However, these devices incur several severe issues for commercialization that result in frequent read/write errors and unnecessary power consumption. To fix the issues that affect the performance of RRAM devices, researchers are proposing various approaches regarding new materials, designs, and properties. Hence, this Special Issue will be considering all RRAM device-related outcomes to help researchers and will publish both original research papers and review papers to contribute to this research topic.

Guest Editor

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Message from the Editor-in-Chief

Electronics is a multidisciplinary journal designed to appeal to a diverse audience of research scientists, practitioners, and developers in academia and industry. The journal is devoted to fast publication of latest technological breakthroughs, cutting-edge developments, and timely reviews of current and emerging technologies related to the broad field of electronics. Experimental and theoretical results are published as regular peer-reviewed articles or as articles within Special Issues guestedited by leading experts in selected topics of interest.

Editor-in-Chief

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